CLAIMS

- 1. A method for producing micromachined devices for use in Microelectromechanical Systems (MEMS), comprising the steps of:
- 5 providing a crystalline wafer with a front plane,

processing from said wafer at least one micromachined device comprising at least one elongated opening or cavity, the opening or cavity having a longitudinal axis, so that an angle is formed by said longitudinal axis and a line formed by intersection of the front plane of the wafer and a cleavage plane, said cleavage plane being defined as a plane along which cleavage of the wafer is most likely to occur.

- 2. A method according to claim 1, wherein said wafer has a shape of a circular disc, with at least one part cut off along a chord of said circular disc, the longest of said chords being a flat of said wafer.
- **3.** A method according to claim 2 wherein said flat is not parallel to said intersection.
- 4. A method according to claim 2, wherein said flat is parallel to said intersection.
 - **5.** A method according to claim 4, wherein said wafer has a back plane,
- wherein said wafer is a silicon wafer, whose front and back planes are oriented along a plane of the {100} family, and

wherein said cleavage plane is a plane belonging to the {111} family.

- 6. A method according to claim 5, wherein said angle is less than
- **25** 45°.

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- 7. A method according to claim 4, wherein said wafer is a silicon wafer, whose front and back surfaces are oriented along a plane of the {100} family and wherein said cleavage plane is a plane belonging to the {110} family.
- 8. A method according to claim 7, wherein said angle is less than30 45°.
 - **9.** A method according to claim 4, wherein said processing comprises the steps of:

subjecting said wafer to a photolithography step, whereby a pattern is printed through a mask onto said wafer; and

etching said wafer,

characterised in that said photolithography step comprises the step of rotating said mask 5 over an angle with respect to said wafer.

- 10. A method according to claim 9, wherein said photolithography step comprises a contact printing step.
- 11. A method according to claim 9, wherein said photolithography step comprises a proximity printing step.
- 10 12. A method according to claim 4, wherein said processing comprises the steps of:

subjecting said wafer to a photolithography step, whereby a pattern is printed through a mask onto said wafer;

etching said wafer,

- wherein said pattern is positioned at an angle with respect to said mask.
 - 13. A method according to claim 12, wherein said photolithography step comprises a contact printing step.
 - 14. A method according to claim 12, wherein said photolithography step comprises a proximity printing step.
- 20 15. A method according to claim 4, wherein said processing comprises the steps of:

subjecting said wafer to a photolithography step, whereby a pattern is printed through a mask onto said wafer;

etching said wafer.

- characterised in that said photolithography step comprises the step of rotating said wafer over an angle with respect to said mask.
 - 16. A method according to claim 15, wherein said photolithography step comprises a contact printing step.
- 17. A method according to any claim 15, wherein said 30 photolithography step comprises a proximity printing step.
 - **18.** A method according to claim 3, wherein said processing comprises the steps of:

subjecting said wafer to a photolithography step, whereby a pattern is printed through a mask onto said wafer,

etching said wafer.

- 19. A method according to claim 18, wherein said5 photolithography step comprises a number of projection printing steps.
 - 20. A method according to claim 18, wherein said photolithography step comprises a contact printing step.
 - 21. A method according to claim 18, wherein said photolithography step comprises a proximity printing step.
- 10 22. A micromachined device for use in Microelectromechanical Systems, said device being produced according to the method described in claim 1.
- Microelectromechanical Systems, said device being produced according to the method described in claim 1.